AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116 - EXPEDITED PROCEDURE

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Title:

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METHOD FOR FORMING A STORAGE CELL CAPACITOR COMPATIBLE WITH HIGH DIELECTRIC CONSTANT MATERIALS

- 52. The [electrode] dynamic random access memory device as specified in (Amended) Claim 51, wherein said second portion and said third portion are different materials.
- 53. The [electrode]dynamic random access memory device as specified in (Amended) Claim 52, wherein said first portion and said third portion are different materials.
- 105. (Amended) A dynamic random access memory device comprising: a capacitor including an electrode which comprises:
 - a first portion formed in an insulative layer having an upper surface; a)
 - a second portion overlying the first portion and having a sidewall b) substantially flush with the upper surface; and
 - a third portion overlying the second portion and, extending above and c) below the upper surface of the insulative layer, and including a recess, wherein the first portion and the second portion are different materials.
- The [electrode of] dynamic random access memory device as specified in 106. (Amended) Claim 105, wherein the second portion and the third portion are different materials.
- 107. The [electrode of] dynamic random access memory device as specified in (Amended) Claim 105, wherein the first portion and the third portion are different materials.
- 113. (Amended) The electrode of Claim 112, wherein the contact contacts the diffusion barrier portion, and the diffusion barrier portion contacts the oxidation resistant portion.